

## Refine Search

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Terms	Documents
L1 and LDMOS	1

Database:

US Pre-Grant Publication Full-Text Database  
**US Patents Full-Text Database**  
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 EPO Abstracts Database  
 JPO Abstracts Database  
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Search:

L7





### Search History

DATE: Tuesday, November 08, 2005    [Printable Copy](#)    [Create Case](#)

<u>Set</u> <u>Name</u> side by side	<u>Query</u>	<u>Hit</u> <u>Count</u>	<u>Set</u> <u>Name</u> result set
<i>DB=USPT; PLUR=YES; OP=OR</i>			
<u>L7</u>	L1 and LDMOS	1	<u>L7</u>
<u>L6</u>	MOSFET and (("multilayered" near8 contact) same (via or feedthrough))	6	<u>L6</u>
<u>L5</u>	L4 and via	2	<u>L5</u>
<u>L4</u>	metalization and "multilayered contact"	5	<u>L4</u>
<u>L3</u>	L2 and mosfet	0	<u>L3</u>
<u>L2</u>	"multilayered contact"	19	<u>L2</u>
<u>L1</u>	6707102	1	<u>L1</u>

END OF SEARCH HISTORY

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